

Amendments to the Specification

Please add the following new paragraph before the heading at page 10, line 16:

Figs. 3A to 3D are perspective views of a plane of an insulating layer and graphs of the volume resistivity thereof.

Please replace the paragraph beginning on page 15, line 2, with the following rewritten paragraph:

After forming the electrode for the electrostatic adsorption 3 and the heating layer 4 in both sides of the supporting substrate 1 as described above, the heating apparatus 6 which has an electrostatic adsorption function can be obtained by forming the insulating layer 5 so that it may cover the electrode for electrostatic adsorption 3 and the heating layer 4. At that time, the insulating layer is formed so that the volume resistivity of the insulating layer 5 is varied in a plane, according to the present invention (Fig. 2 (d) and Fig. 3A to Fig. 3D).

Please replace the paragraph beginning on page 15, line 20, with the following rewritten paragraph:

More specifically, referring to Fig. 3Figs. 3A to 3D, the volume resistibility in a plane 10, 12 of the insulating layer can be varied at a distribution such that it may be low at a center part 14, 16 and high at a peripheral part 15, 17 in the shape of a concentric circle 11, 13 by supplying the dope gas from a nozzle directed to the center part of the substrate when the insulating layer 5 is deposited by a CVD method. By depositing in such a way, a dopant concentration becomes high at a center part and becomes low at a peripheral part. On the contrary, the dopant concentration can be made high at a peripheral part by supplying the dope gas from the peripheral part. Alternatively, by arranging two or more nozzles, a dopant concentration can be varied at each nozzle. In the case of a sintering method, the impurities can be mixed therein with varying an amount of impurities partially when a sintering is performed.